

ROHSV EARTH FRIEND

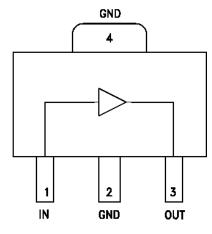
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Typical Applications

The HMC740ST89E is ideal for:

- Cellular/3G & WiMAX/4G
- Fixed Wireless & WLAN
- CATV, Cable Modem & DBS
- Microwave Radio & Test Equipment
- IF & RF Applications

Functional Diagram



HMC740ST89E

InGaP HBT ACTIVE BIAS MMIC AMPLIFIER, 0.05 – 3 GHz

Features

P1dB Output Power: +18 dBm Gain: 15 dB Output IP3: +40 dBm Cascadable 50 Ohm I/Os Single Supply: +5V Industry Standard SOT89 Package Robust 1000V ESD, Class 1C Stable Current Over Temperature Active Bias Network

General Description

The HMC740ST89E is an InGaP Heterojunction Bipolar Transistor (HBT) Gain Block MMIC SMT amplifier covering 0.05 to 3 GHz. Packaged in an industry standard SOT89, the amplifier can be used as a cascadable 50 Ohm RF or IF gain stage as well as a PA or LO driver with up to +18 dBm output power. The HMC740ST89E offers 15 dB of gain with a +40 dBm output IP3 at 100 MHz, and can operate directly from a +5V supply. The HMC740ST89E exhibits excellent gain and output power stability over temperature, while requiring a minimal number of external bias components.

Electrical Specifications, Vcc = 5V, T_{A} = +25° C Parameter Min Тур. Max. Min. Max. Units Typ **Frequency Range** 0.05 - 1 0.05 - 3 GHz Gain 12 15 11 15 dB Gain Flatness ±0.1 ±0.7 dB Gain Variation over Temperature 0.006 0.003 0 006 dB/ °C 0.003 Input Return Loss 15 dB 18 Output Return Loss 18 18 dB **Reverse Isolation** 20 21 dB Output Power for 1 dB Compression (P1dB) 17 15.5 18 14.5 dBm Output Third Order Intercept (IP3) 38 32 dBm (Pout= 0 dBm per tone, 1 MHz spacing) Noise Figure 3.5 3.5 dB Supply Current (Icq) 88 88 mA

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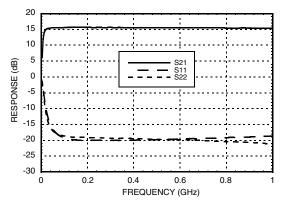


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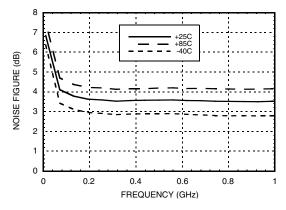
ROHS V

IF Band Performance

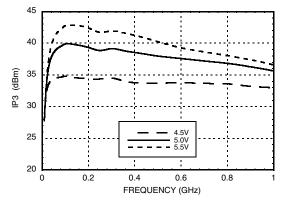
Gain & Return Loss



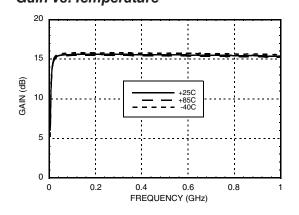
Noise Figure vs. Temperature



Output IP3 vs. Vcc



Gain vs. Temperature

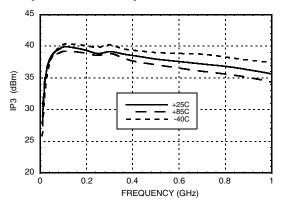


HMC740ST89E

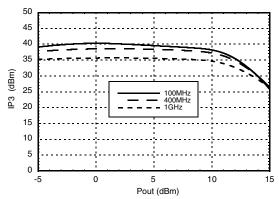
InGaP HBT ACTIVE BIAS

MMIC AMPLIFIER, 0.05 – 3 GHz

Output IP3 vs. Temperature



Output IP3 vs. Output Power



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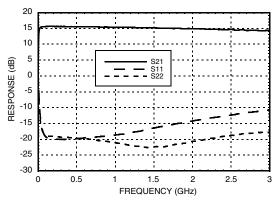
HMC740ST89E

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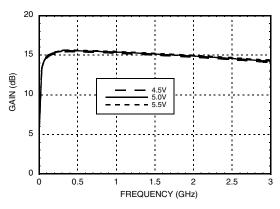


Broadband Performance

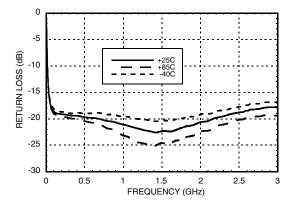
Gain & Return Loss



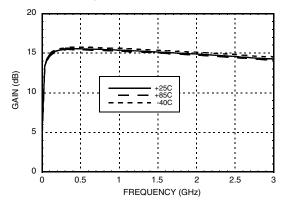
Gain vs. Vcc



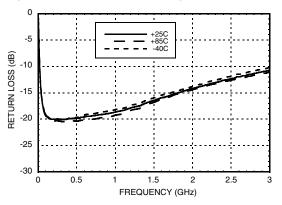
Output Return Loss vs. Temperature



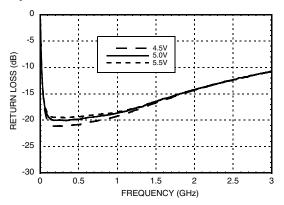
Gain vs. Temperature



Input Return Loss vs. Temperature



Input Return Loss vs. Vcc



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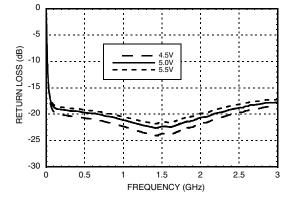


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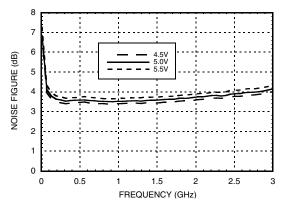


Output Return Loss vs. Vcc

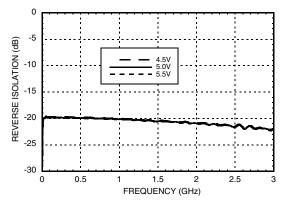


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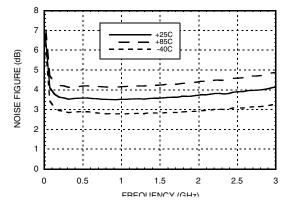
Noise Figure vs. Vcc



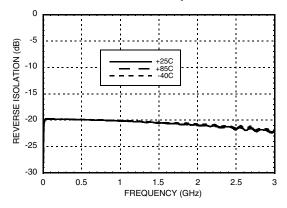
Reverse Isolation vs. Vcc



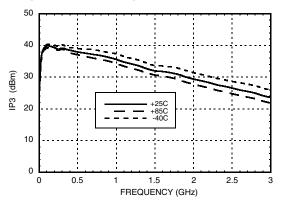
Noise Figure vs. Temperature



Reverse Isolation vs. Temperature



Output IP3 vs. Temperature



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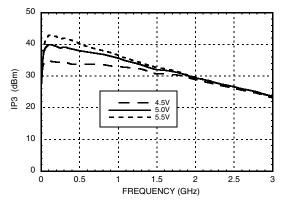
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MMIC AMPLIFIER, 0.05 - 3 GHz

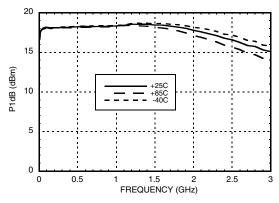
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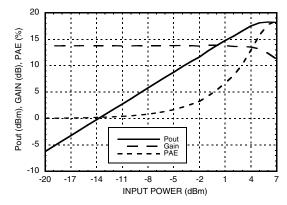
Output IP3 vs. Vcc



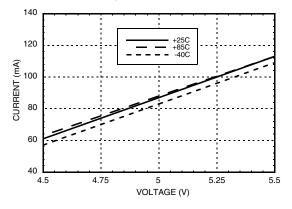
P1dB vs. Temperature



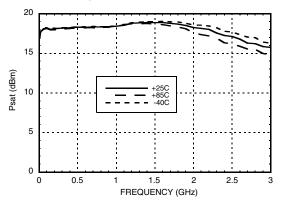
Power Compression @ 500 MHz



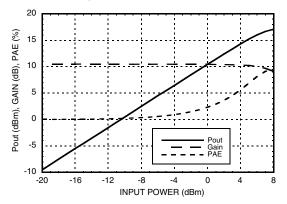
Current vs. Temperature



Psat vs. Temperature



Power Compression @ 2 GHz



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Absolute Maximum Ratings

Collector Bias Voltage (Vcc)	+5.5 Vdc		
RF Input Power (RFIN)	N) +15 dBm		
Junction Temperature	150 °C		
Continuous Pdiss (T = 85 °C) (derate 10.23 mW/°C above 85 °C)	0.66 W		
Thermal Resistance (junction to lead)	97.78 °C/W		
Storage Temperature	-65 to +150 °C		
Operating Temperature	-40 to +85 °C		
ESD Sensitivity (HMB)	Class 1C		



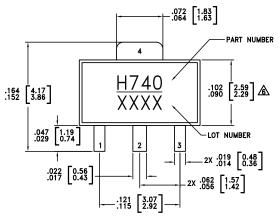
ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

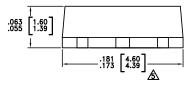
MMIC AMPLIFIER, 0.05 - 3 GHz

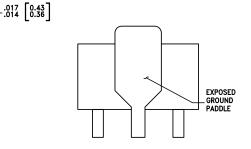
HMC740ST89E

InGaP HBT ACTIVE BIAS

Outline Drawing







NOTES:

1 PACKAGE B

1. PACKAGE BODY MATERIAL: MOLDING COMPOUND MP-180S OR EQUIVALENT.

MOLDING COMPOUND MP-180S OR EQUIVALENT.

2. LEAD MATERIAL: Cu w/ Ag SPOT PLATING.

3. LEAD PLATING: 100% MATTE TIN.
4. DIMENSIONS ARE IN INCHES [MILLIMETERS]

A. DIMENSIONS ARE IN INCRES [IMILLIMETERS]

<u>A</u>DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.1511111 FER SIDE.

7. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[1]
HMC740ST89E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 ^[2]	<u>H740</u> XXXX

[1] 4-Digit lot number XXXX

[2] Max peak reflow temperature of 260 °C

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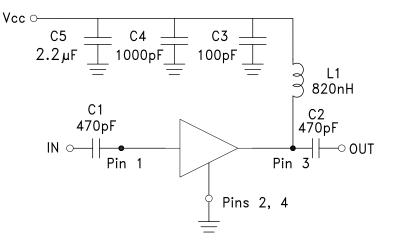


InGaP HBT ACTIVE BIAS MMIC AMPLIFIER, 0.05 – 3 GHz

Pin Descriptions

Pin Number	Function	Description	Interface Schematic	
1	IN	This pin is DC coupled. An off chip DC blocking capacitor is required.		
3	OUT	RF output and DC Bias (Vcc) for the output stage.		
2, 4	GND	These pins and package bottom must be connected to RF/DC ground.		

Application Circuit



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